SamHop Microelectronics Corp.

STS2621

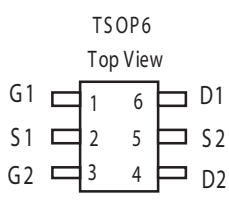
Jun.6 2005

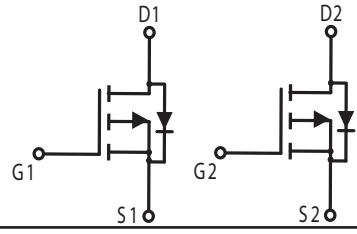
Dual P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) MAX
-20V	-2A	130 @ V_{GS} = -4.5V
		190 @ V_{GS} = -2.5V

FEATURES

- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- SOT-26 Package.





ABSOLUTE MAXIMUM RATINGS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±10	V
Drain Current-Continuous [a] @ T_C=25°C	I_D	-2	A
-Pulsed [b]	I_{DM}	-7	A
Drain-Source Diode Forward Current [a]	I_S	-1.25	A
Maximum Power Dissipation [a]	P_D	1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient [a]	$R_{\theta JA}$	125	°C/W

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ELECTRICAL CHARACTERISTICS (T_A =25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ [c]	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=-250uA	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V, V_{GS}=0V			1	uA
Gate-Body Leakage	I_{GSS}	V_{GS}=± 10V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS [b]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250uA	-0.5	-0.8	-1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D= -2.0A		115	130	m-ohm
		V_{GS}= -2.5V, I_D= -1.0A		175	190	m-ohm
On-State Drain Current	$I_{D(ON)}$	V_{DS}= -5V, V_{GS}= -4.5V	-5			A
Forward Transconductance	g_{FS}	V_{DS}= -5V, I_D=-2A		6		S
DYNAMIC CHARACTERISTICS [c]						
Input Capacitance	C_{ISS}	V_{DS}= -20V, V_{GS}= 0V f=1.0MHz		295		pF
Output Capacitance	C_{OSS}			63		pF
Reverse Transfer Capacitance	C_{RSS}			52		pF
SWITCHING CHARACTERISTICS [c]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD}= -10V, I_D= -1A, V_{GS}= -4.5V, R_{GEN}= 6 ohm		11.5		ns
Rise Time	t_r			15.6		ns
Turn-Off Delay Time	$t_{D(OFF)}$			83.1		ns
Fall Time	t_f			43.6		ns
Total Gate Charge	Q_g	V_{DS}= -10V, I_D= -2A, V_{GS}= -4.5V		3.5		nC
Gate-Source Charge	Q_{gs}			0.9		nC
Gate-Drain Charge	Q_{gd}			1.1		nC

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ[c]	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [b]						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =-1.25A		-0.85	-1.2	V

Notes

a.Surface Mounted on FR4 Board, t≤10sec.
b.Pulse Test:Pulse Width≤300us, Duty Cycle≤2%.
c.Guaranteed by design, not subject to production testing.

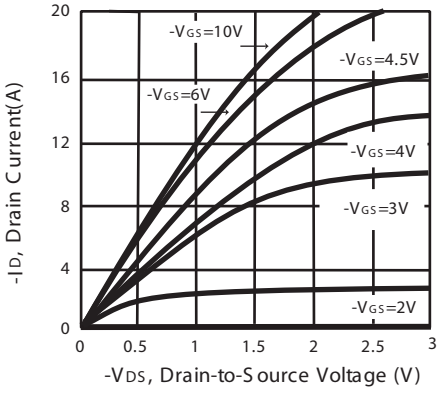


Figure 1. Output Characteristics

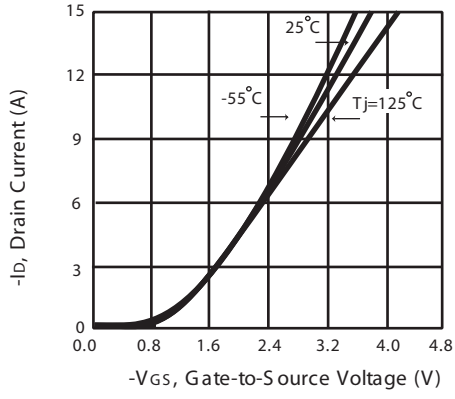


Figure 2. Transfer Characteristics

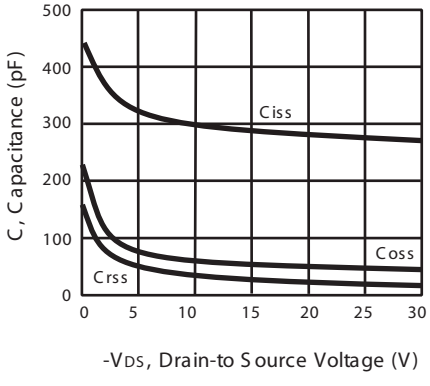


Figure 3. Capacitance

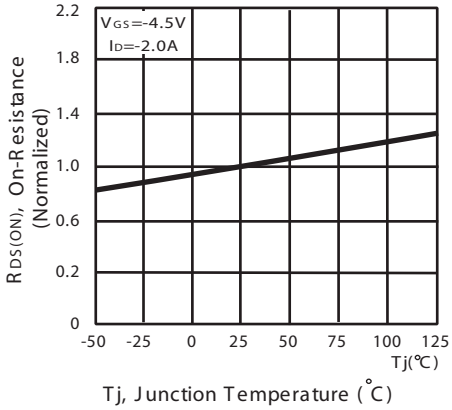
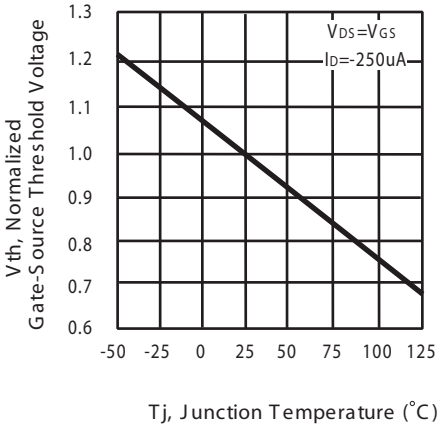


Figure 4. On-Resistance Variation with Temperature



with Temperature

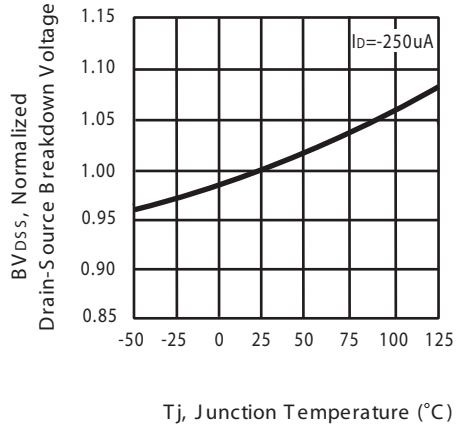


Figure 6. Breakdown Voltage Variation with Temperature

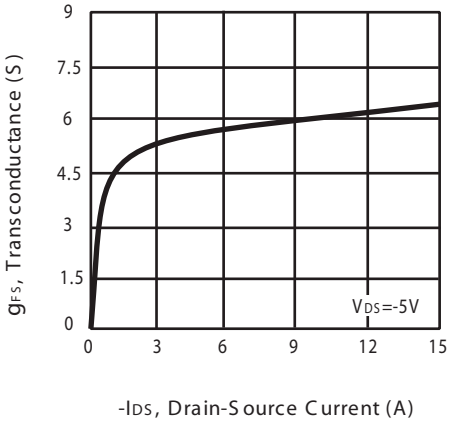


Figure 7. Transconductance Variation with Drain Current

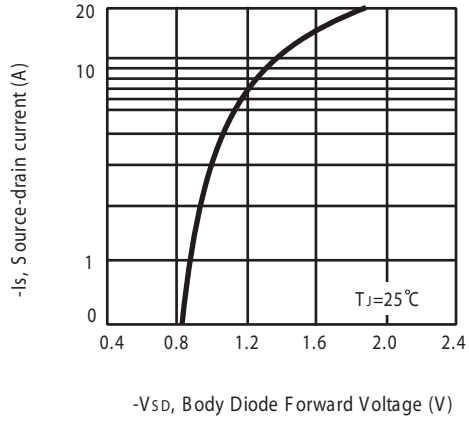


Figure 8. Body Diode Forward Voltage Variation with Source Current

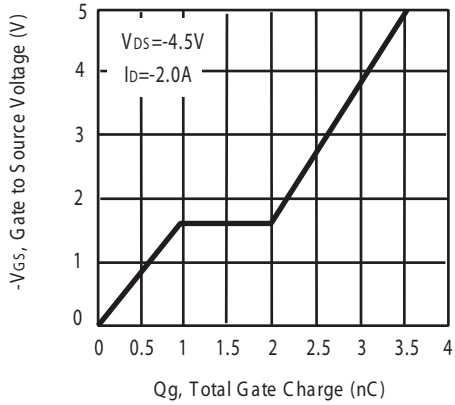


Figure 9. Gate Charge

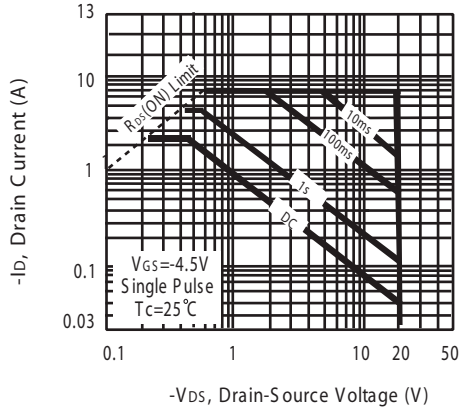


Figure 10. Maximum Safe Operating Area

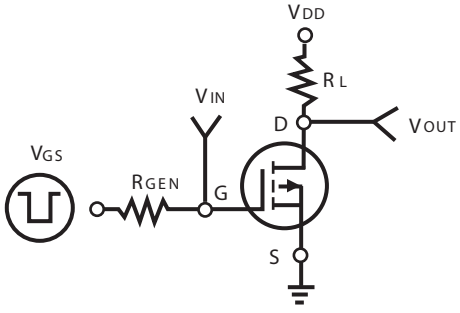


Figure 11. Switching Test Circuit

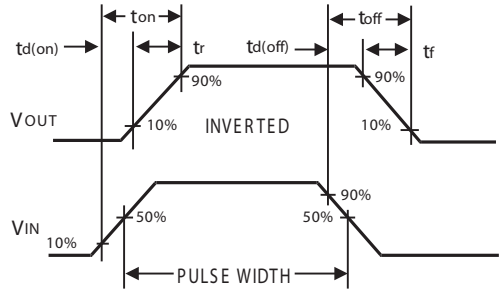
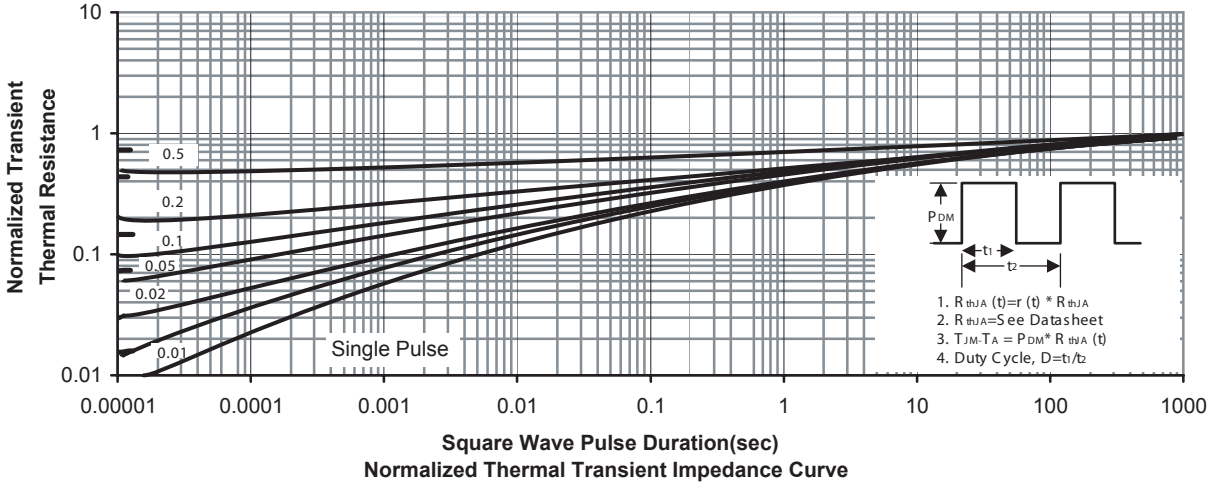


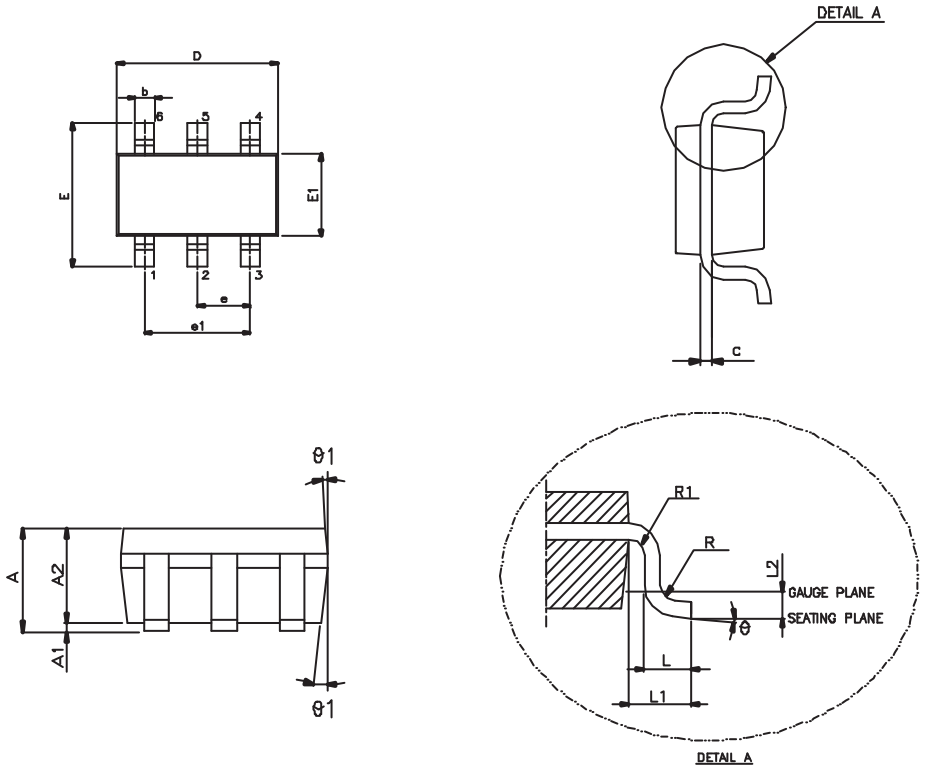
Figure 12. Switching Waveforms



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PACKAGE OUTLINE DIMENSIONS

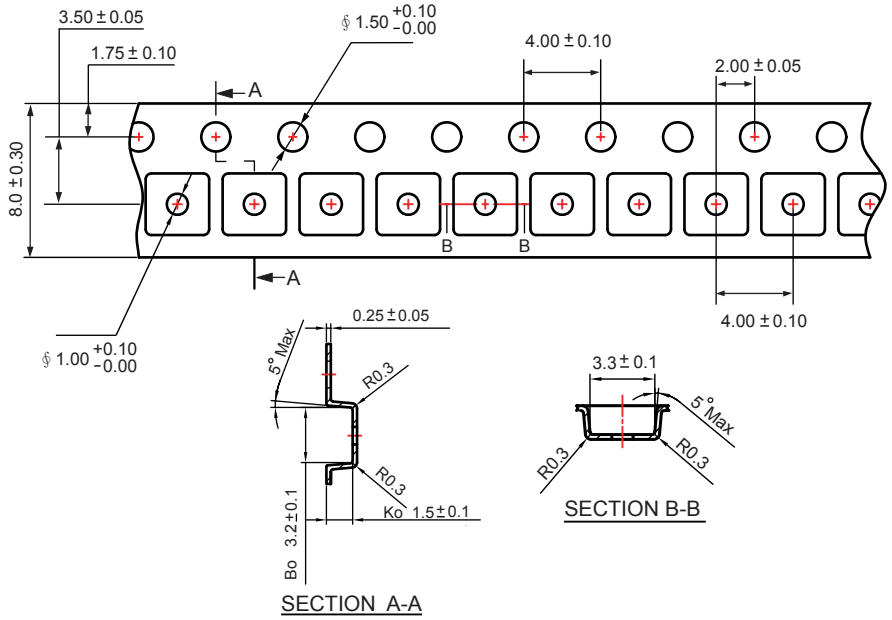
TSOP6



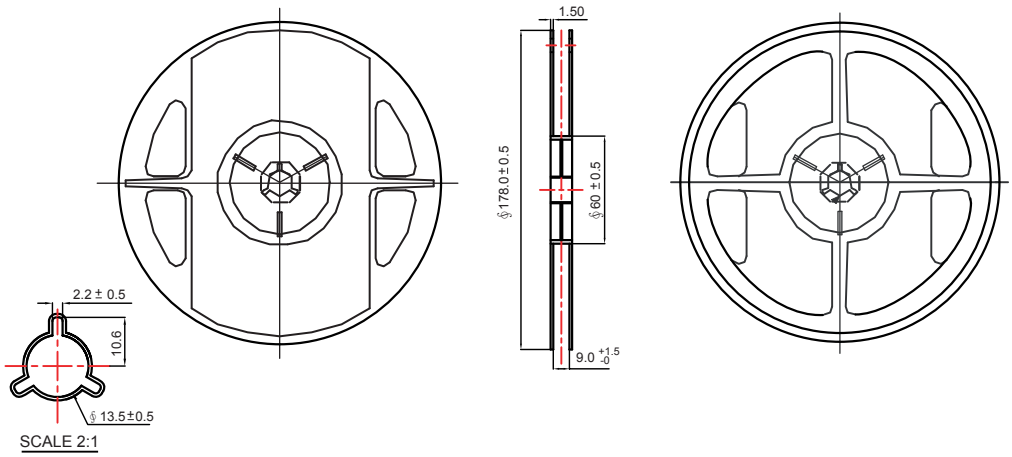
SYMBOL	MIN.	NOM.	MAX.
A	–	–	1.45
A1	–	–	0.15
A2	0.90	1.15	1.30
b	0.30	–	0.50
c	0.08	–	0.22
D		2.90 BSC.	
E		2.80 BSC.	
E1		1.60 BSC.	
e		0.95 BSC	
e1		1.90 BSC.	
L	0.30	0.45	0.60
L1		0.60 REF.	
L2		0.25 BSC.	
R	0 10	–	–
R1	0 10	–	0.25
θ	0°	4°	8°
θ1	5°	10°	15°

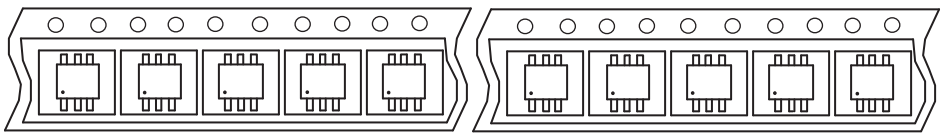
TSOP6 Tape and Reel Data

TSOP6 Carrier Tape



TSOP6 Reel





SOT 26